

2N2063A
Transistor, Bipolar, GE
PNP Power

Military/High-Rel : **N**

V(BR)CEO (V) : **20**

V(BR)CBO (V) : **40**

I(C) Max. (A) : **5.0**

Absolute Max. Power Diss. (W) : **90#**

Maximum Operating Temp (ω C) : **100#**

I(CBO) Max. (A) : **2.0m**

@V(CBO) (V) (Test Condition) : **40**

V(CE)sat Max. (V) : **1.0**

@I(C) (A) (Test Condition) : **5.0**

@I(B) (A) (Test Condition) : **500m**

h(FE) Min. Current gain. : **20**

h(FE) Max. Current gain. : **60**

@I(C) (A) (Test Condition) : **2.0**

@V(CE) (V) (Test Condition) : **2.0**

f(T) Min. (Hz) Transition Freq : **5.0k**

@I(C) (A) (Test Condition) : **2.0**

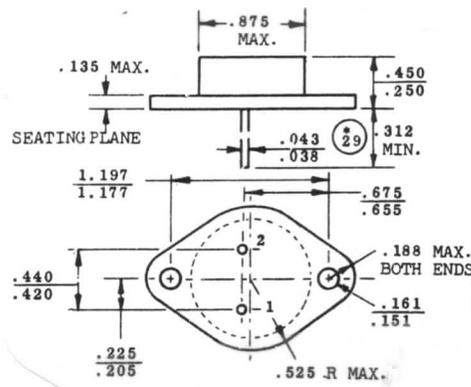
@V(CE) (V) (Test Condition) : **2.0**

t(r) Max. (s) Rise time : **18u**

t(f) Max. (s) Fall time. : **9.0u**

Package Style : **TO-3**

Mounting Style : **T**



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